

**IN THE CLAIMS:**

Please amend the claims as follows:

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A1 11. (Amended) The method according to claim 1, wherein the sequentially etching step further forms a line along a boundary between the first region and a second region of the semiconductor substrate by removing the third insulation layer and of the second insulation layer.

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A2 14. (Amended) The method according to claim 13 wherein the wet station is a bath type.

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15. (Amended) The method according to claim 13 wherein the wet station employs an IPA vapor drier.

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**Attached is a marked up copy showing the changes made.**